



DXT5401

150V PNP SMALL SIGNAL TRANSISTOR IN SOT89

Features

- BV_{CEO} > -150V
- I_C = -600mA high Collector Current
- Ideal for Medium Power Switching or Amplification Applications
- Complementary NPN Type: DXT5551
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208@3
- Weight: 0.055 grams (Approximate)

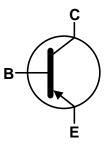
Applications

- Amplifiers
- Power Supplies

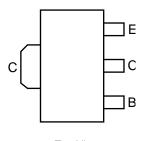
SOT89



Top View



Device Symbol



Top View Pin-Out

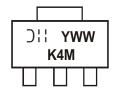
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXT5401-13	Standard	K4M	13	12	3.000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current	lc	-600	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @T _A = +25°C (Note 5)	P_{D}	1	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{ hetaJA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С
Notes: 5. For a device mounted with the collector lead on minimum recommended pad (MRP) layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device				

is measured under still air conditions whilst operating in a steady-state.

^{6.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information

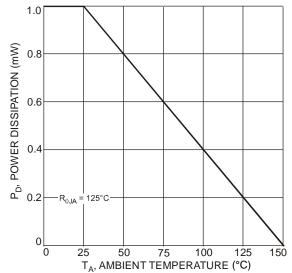


Fig. 1 Max Power Dissipation vs. Ambient Temperature



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-160		V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-150		V	$I_C = -1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0		V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	lone		-50	nA	$V_{CB} = -120V, I_{E} = 0$
Collector Cutoff Cuttern	I _{CBO}			μΑ	$V_{CB} = -120V$, $I_E = 0$, $T_A = +100^{\circ}C$
Emitter Cutoff Current	I _{EBO}	_	-50	nA	$V_{EB} = -3.0V, I_C = 0$
ON CHARACTERISTICS (Note 7)					
		50	_		$V_{CE} = -5.0V, I_{C} = -1.0mA$
DC Current Gain	h _{FE}	60	240	_	$V_{CE} = -5.0V, I_{C} = -10mA$
		50	_		$V_{CE} = -5.0V, I_{C} = -50mA$
Collector-Emitter Saturation Voltage	Variour	SAT) —	-0.2	V	$I_C = -10mA$, $I_B = -1.0mA$
Concetor Emitter Cataration Voltage	V _{CE(SAT)}		-0.5		$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	-1.0	V	$I_C = -10mA$, $I_B = -1.0mA$
o a constant of the constant o					$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_obo	_	6.0	pF	$V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$
Small Signal Current Gain	h _{fe}	40	260		$V_{CE} = -10V$, $I_{C} = -1.0$ mA, $f = 1.0$ kHz
Current Gain-Bandwidth Product	f _T	100	300	MHz	$V_{CE} = -10V$, $I_{C} = -10mA$, $f = 100MHz$
Noise Figure	NF	_	8.0	dB	$V_{CE} = -5.0V$, $I_{C} = -200\mu A$, $R_{S} = 10\Omega$, $f = 1.0kHz$

Notes: 7. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

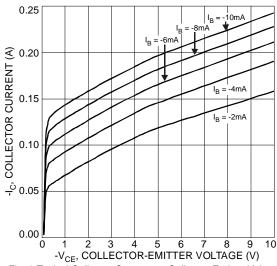


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

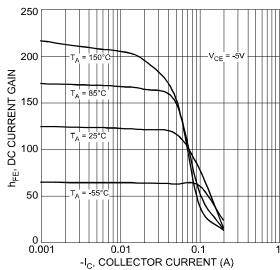


Fig. 3 Typical DC Current Gain vs. Collector Current



Typical Electrical Characteristics (Continued)

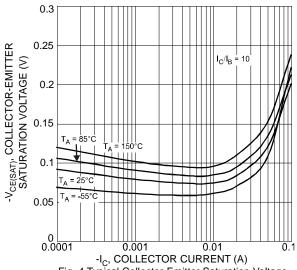


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

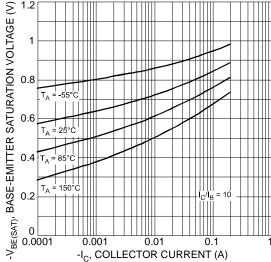


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

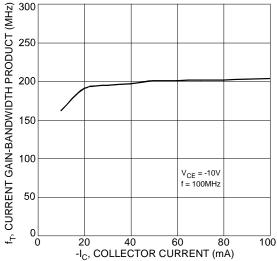


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

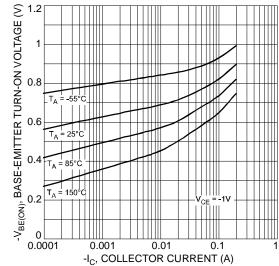


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

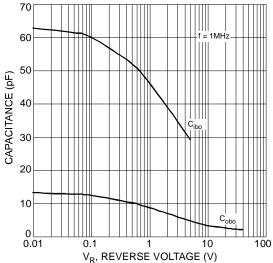


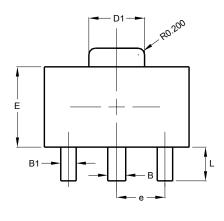
Fig. 7 Typical Capacitance Characteristics

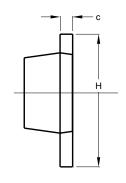


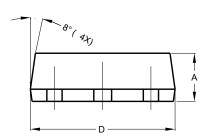
Package Outline Dimensions

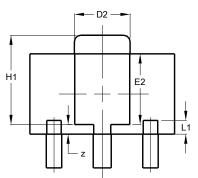
Please see http://www.diodes.com/package-outlines.html for the latest version.

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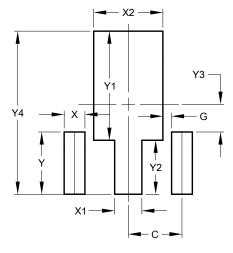


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Η	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value (in mm)
С	1.500
G	0.244
Χ	0.580
X1	0.760
X2	1.933
Υ	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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